

MMBF2201N, NVF2201N

Power MOSFET 300 mAmps, 20 Volts

N-Channel SC-70/SOT-323

These miniature surface mount MOSFETs low $R_{DS(on)}$ assure minimal power loss and conserve energy, making these devices ideal for use in small power management circuitry. Typical applications are dc-dc converters, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

Features

- Low $R_{DS(on)}$ Provides Higher Efficiency and Extends Battery Life
- Miniature SC-70/SOT-323 Surface Mount Package Saves Board Space
- NVF Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable*
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	20	Vdc
Gate-to-Source Voltage - Continuous	V_{GS}	± 20	Vdc
Drain Current			mAdc
- Continuous @ $T_A = 25^\circ\text{C}$	I_D	300	
- Continuous @ $T_A = 70^\circ\text{C}$	I_D	240	
- Pulsed Drain Current ($t_p \leq 10 \mu\text{s}$)	I_{DM}	750	
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ (Note 1) Derate above 25°C	P_D	150 1.2	mW mW/ $^\circ\text{C}$
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	833	$^\circ\text{C}/\text{W}$
Maximum Lead Temperature for Soldering Purposes, for 10 seconds	T_L	260	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Mounted on G10/FR4 glass epoxy board using minimum recommended footprint.

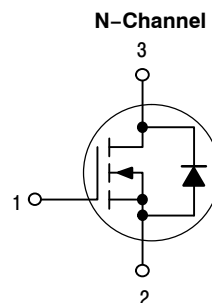


ON Semiconductor®

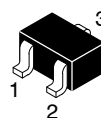
<http://onsemi.com>

300 mAmps, 20 Volts

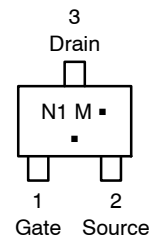
$R_{DS(on)} = 1 \Omega$



MARKING DIAGRAM AND PIN ASSIGNMENT



SC-70/SOT-323
CASE 419
STYLE 8



N1 = Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBF2201NT1G	SOT-323 (Pb-Free)	3000 / Tape & Reel
NVF2201NT1G*	SOT-323 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBF2201N, NVF2201N

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit	
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage (V _{GS} = 0 Vdc, I _D = 10 μA)	V _{(BR)DSS}	20	-	-	Vdc	
Zero Gate Voltage Drain Current (V _{DS} = 16 Vdc, V _{GS} = 0 Vdc) (V _{DS} = 16 Vdc, V _{GS} = 0 Vdc, T _J = 125°C)	I _{DSS}	-	-	1.0 10	μAdc	
Gate-Body Leakage Current (V _{GS} = ± 20 Vdc, V _{DS} = 0)	I _{GSS}	-	-	±100	nAdc	
ON CHARACTERISTICS (Note 2)						
Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = 250 μAdc)	V _{GS(th)}	1.0	1.7	2.4	Vdc	
Static Drain-to-Source On-Resistance (V _{GS} = 10 Vdc, I _D = 300 mAdc) (V _{GS} = 4.5 Vdc, I _D = 100 mAdc)	r _{DS(on)}	-	0.75 1.0	1.0 1.4	Ω	
Forward Transconductance (V _{DS} = 10 Vdc, I _D = 200 mAdc)	g _{FS}	-	450	-	mMhos	
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V _{DS} = 5.0 V)	C _{ISS}	-	45	-	pF
Output Capacitance	(V _{DS} = 5.0 V)	C _{OSS}	-	25	-	
Transfer Capacitance	(V _{DG} = 5.0 V)	C _{RSS}	-	5.0	-	
SWITCHING CHARACTERISTICS (Note 3)						
Turn-On Delay Time	(V _{DD} = 15 Vdc, I _D = 300 mAdc, R _L = 50 Ω)	t _{d(on)}	-	2.5	-	ns
Rise Time		t _r	-	2.5	-	
Turn-Off Delay Time		t _{d(off)}	-	15	-	
Fall Time		t _f	-	0.8	-	
Gate Charge (See Figure 5)		Q _T	-	1400	-	pC
SOURCE-DRAIN DIODE CHARACTERISTICS						
Continuous Current	I _S	-	-	0.3	A	
Pulsed Current	I _{SM}	-	-	0.75		
Forward Voltage (Note 3)	V _{SD}	-	0.85	-	V	

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
3. Switching characteristics are independent of operating junction temperature.

TYPICAL CHARACTERISTICS

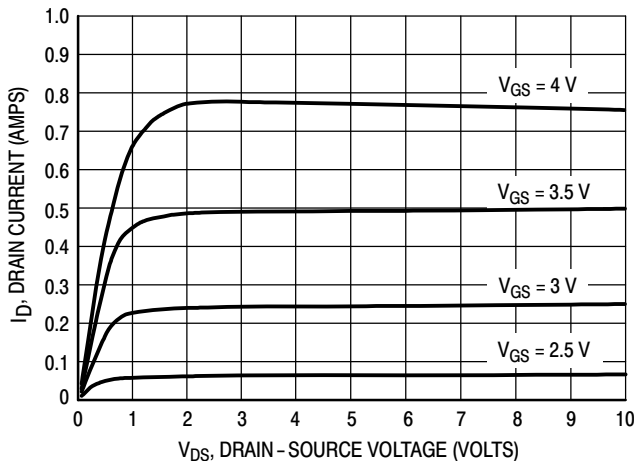


Figure 1. Typical Drain Characteristics

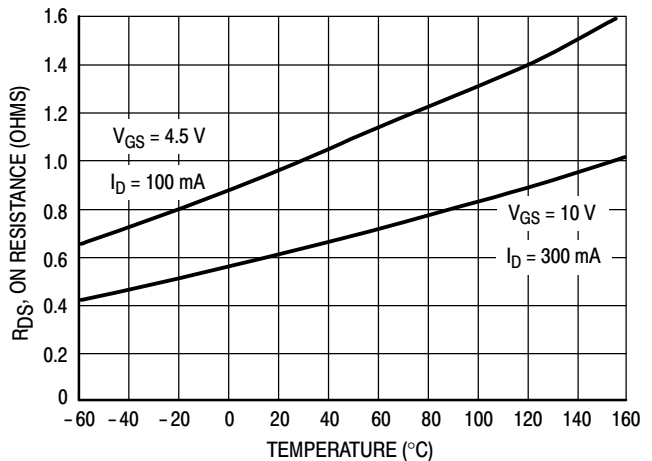


Figure 2. On Resistance versus Temperature

MMBF2201N, NVF2201N

TYPICAL CHARACTERISTICS

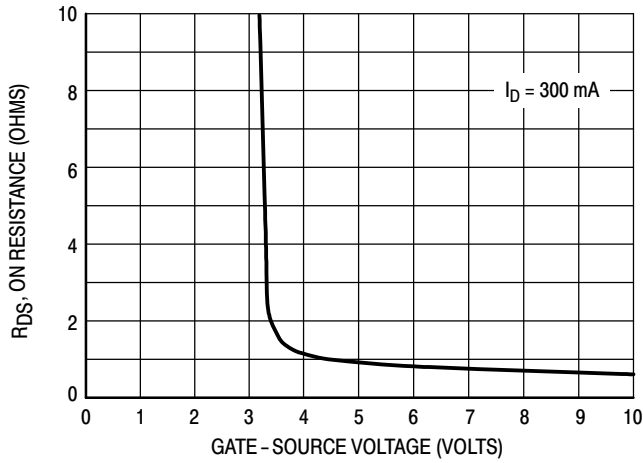


Figure 3. On Resistance versus Gate-Source Voltage

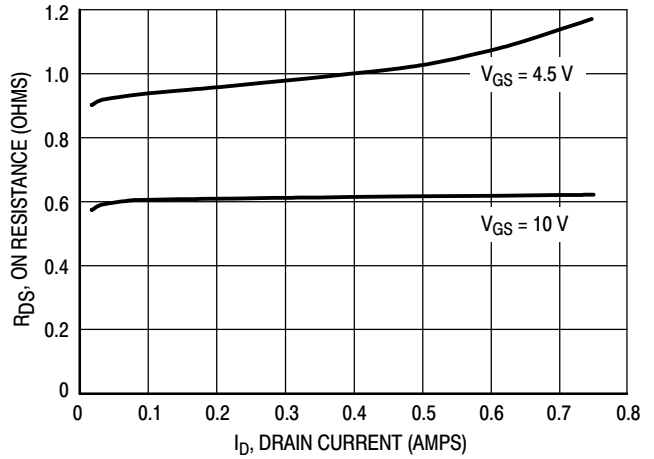


Figure 4. On Resistance versus Drain Current

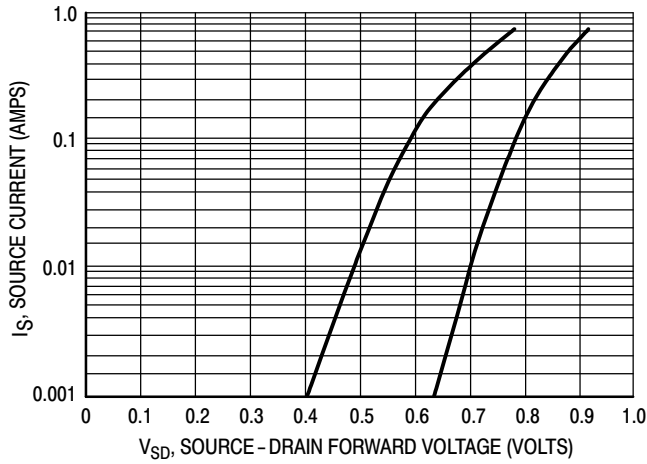


Figure 5. Source-Drain Forward Voltage

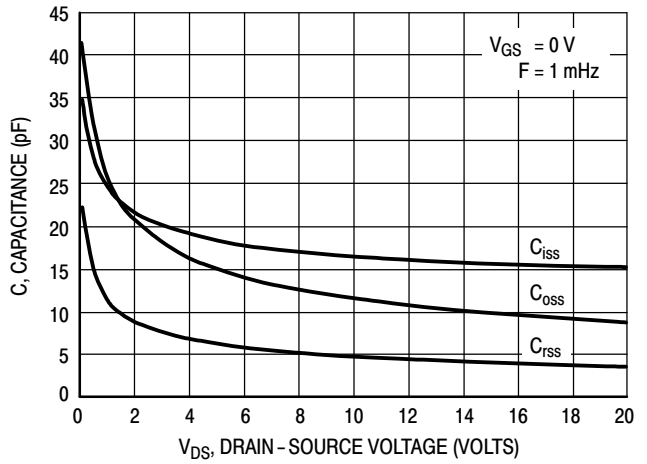


Figure 6. Capacitance Variation

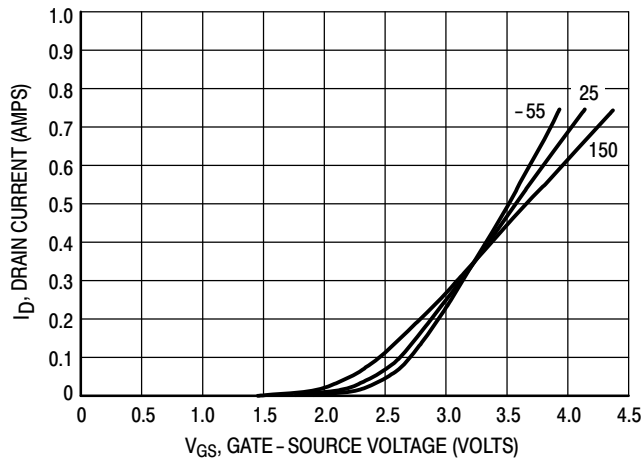


Figure 7. Transfer Characteristics

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 4:1

SC-70 (SOT-323) CASE 419 ISSUE R

DATE 11 OCT 2022



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH

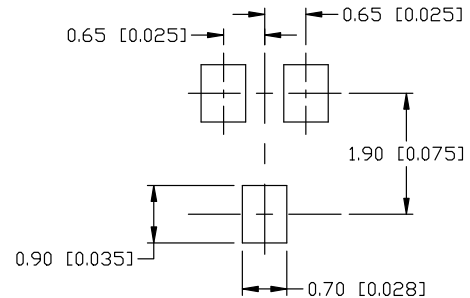
DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
H _E	2.00	2.10	2.40	0.079	0.083	0.095

GENERIC MARKING DIAGRAM



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE
STYLE 6: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 7: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 8: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 9: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 10: PIN 1. CATHODE 2. ANODE 3. ANODE-CATHODE
				STYLE 11: PIN 1. CATHODE 2. CATHODE 3. CATHODE

DOCUMENT NUMBER:	98ASB42819B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SC-70 (SOT-323)	PAGE 1 OF 1

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales